



DRC5123E0L

Silicon NPN epitaxial planar type

For digital circuits

Complementary to DRA5123E

DRC2123E in SMini3 type package

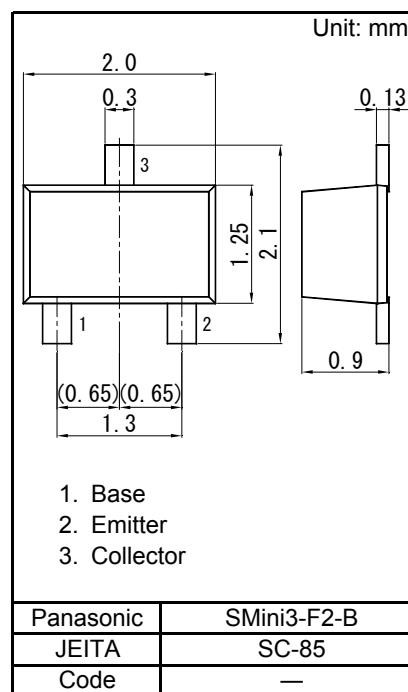
■ Features

- Low collector-emitter saturation voltage $V_{ce(sat)}$
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: N2

■ Packaging

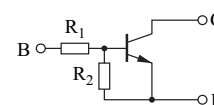
Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)



■ Absolute Maximum Ratings $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	VCBO	50	V
Collector-emitter voltage (Base open)	VCEO	50	V
Collector current	IC	100	mA
Total power dissipation	PT	150	mW
Junction temperature	Tj	150	$^{\circ}\text{C}$
Operating ambient temperature	Topr	-40 to +85	$^{\circ}\text{C}$
Storage temperature	Tstg	-55 to +150	$^{\circ}\text{C}$

Internal Connection



Resistance value	R1	R2	Unit
	2.2	2.2	k Ω

■ Electrical Characteristics $T_a = 25\text{ }^{\circ}\text{C} \pm 3\text{ }^{\circ}\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	VCBO	IC = 10 μA , IE = 0	50			V
Collector-emitter voltage (Base open)	VCEO	IC = 2 mA, IB = 0	50			V
Collector-base cutoff current (Emitter open)	ICBO	VCB = 50 V, IE = 0			0.1	μA
Collector-emitter cutoff current (Base open)	ICEO	VCE = 50 V, IB = 0			0.5	μA
Emitter-base cutoff current (Collector open)	IEBO	VEB = 6 V, IC = 0			2.0	mA
Forward current transfer ratio	hFE	VCE = 10 V, IC = 5 mA	6		20	-
Collector-emitter saturation voltage	VCE(sat)	IC = 10 mA, IB = 0.5 mA			0.3	V
Input voltage	Vi(on)	VCE = 0.2 V, IC = 5 mA	1.8			V
	Vi(off)	VCE = 5 V, IC = 100 μA			0.8	V
Input resistance	R1		-30%	2.2	+30%	k Ω
Resistance ratio	R1/R2		0.8	1.0	1.2	-

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.